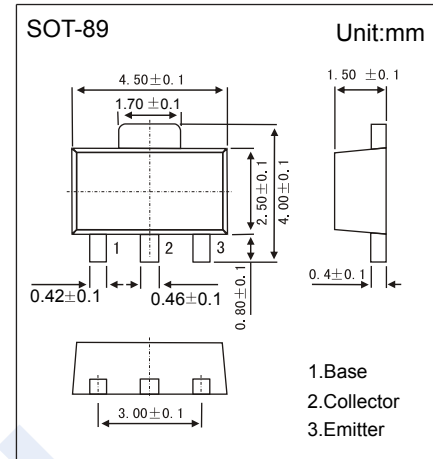
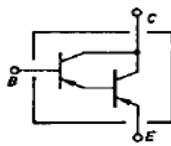


PNP Transistors

2SB1125

■ Features

- Collector Current Capability $I_C = -0.7A$
- Collector Emitter Voltage $V_{CE0} = -50V$
- Complements the 2SD1625

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-80	V
Collector - Emitter Voltage	V_{CE0}	-50	
Emitter - Base Voltage	V_{EB0}	-10	
Collector Current - Continuous	I_C	-0.7	A
Collector Current - Pulse	I_{CP}	-2	
Collector Power Dissipation (Note.1)	P_D	0.5	W
		1.3	
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature range	T_{stg}	-55 to 150	

Note.1: mounted on ceramic substrate (250mm²X0.8mm)

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -100 \mu A, I_E = 0$	-80			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -10 mA, R_{BE} = \infty$	-50			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100 \mu A, I_C = 0$	-10			
Collector-base cut-off current	I_{CB0}	$V_{CB} = -40 V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EB0}	$V_{EB} = -8 V, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100 mA, I_B = -0.1 mA$			-1.2	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100 mA, I_B = -0.1 mA$			-2	
DC current gain	h_{FE}	$V_{CE} = -2 V, I_C = -50 mA$	5000			
		$V_{CE} = -2 V, I_C = -500 mA$	3000			
Collector output capacitance	C_{ob}	$V_{CB} = -10 V, f = 1 MHz$		18		pF
Transition frequency	f_T	$V_{CB} = -5 V, I_C = -50 mA$		170		MHZ

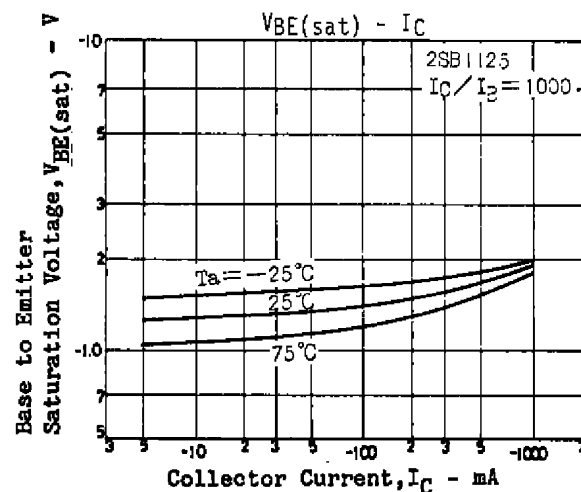
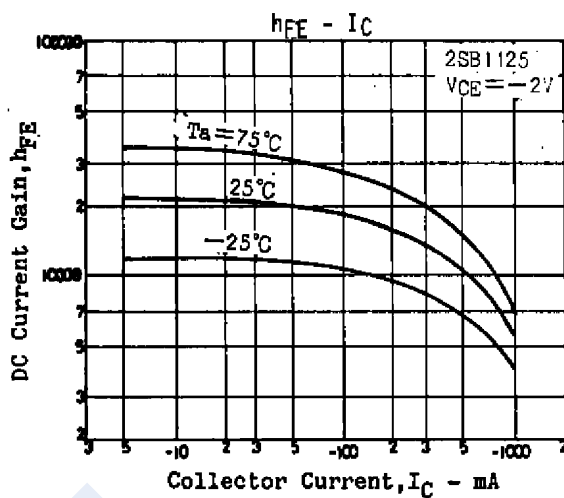
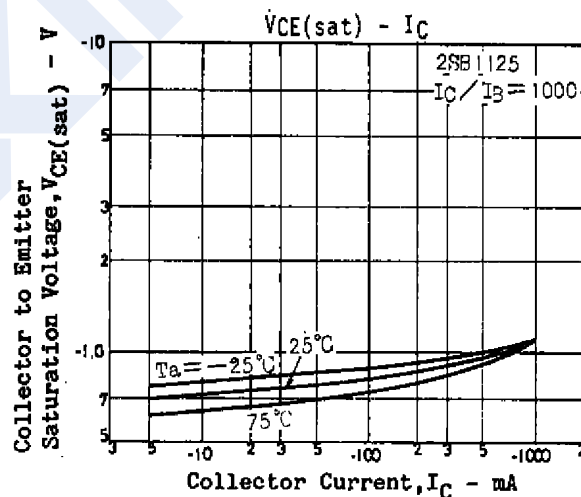
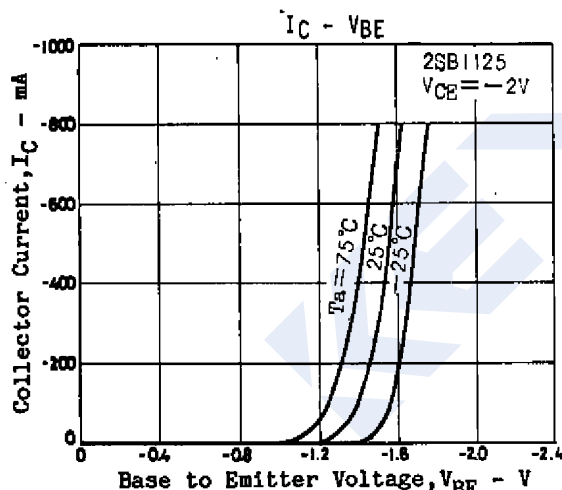
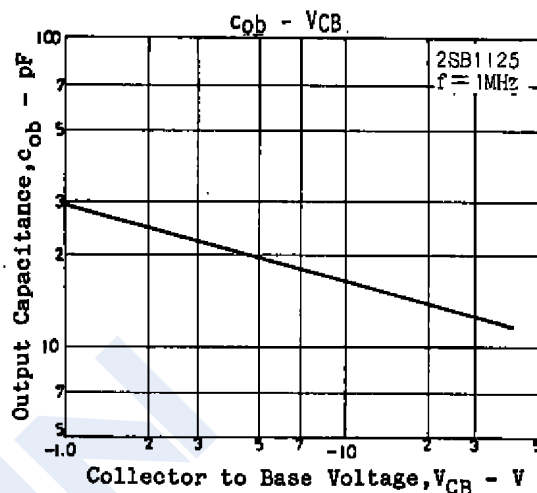
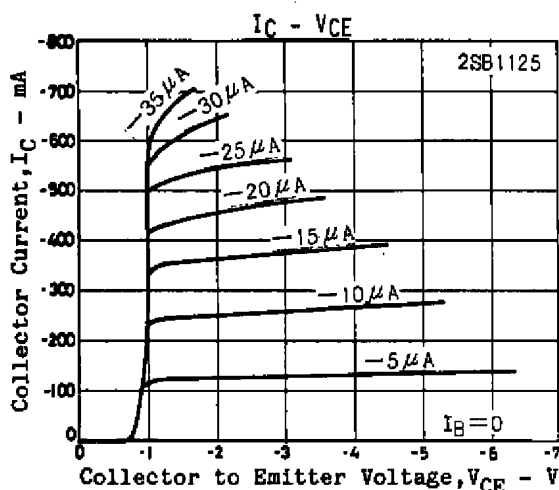
■ Marking

Marking	BH
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PNP Transistors

2SB1125

■ Typical Characteristics



PNP Transistors

2SB1125

■ Typical Characteristics

